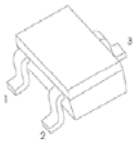
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-523 Plastic-Encapsulate Transistors

SOT-523



1. BASE
2. EMITTER
3. COLLECTOR

2SA1832 TRANSISTOR (PNP)

FEATURES

- High voltage and high current
- Excellent h_{FE} linearity
- Complementary to 2SC4738

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_D	Total Device Dissipation	100	mW
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	125	℃/W
T_J, T_{stg}	Junction and Storage Temperature	-55 to +125	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=-100μA,I_E=0	-50			V
Collector-emitter breakdown voltage	V_{CEO*}	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	V_{EBO}	I_E=-100μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB} =-5V, I_C=0			-100	nA
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-2mA	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA,I_B=-10mA			-0.3	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-1mA	80			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f =1MHz		4	7	pF

CLASSIFICATION OF h_{FE}

Rank	Y	GR
Range	120-240	200-400
Marking	SY	SG